

Update of the fluctuation model

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4-8 October 2010

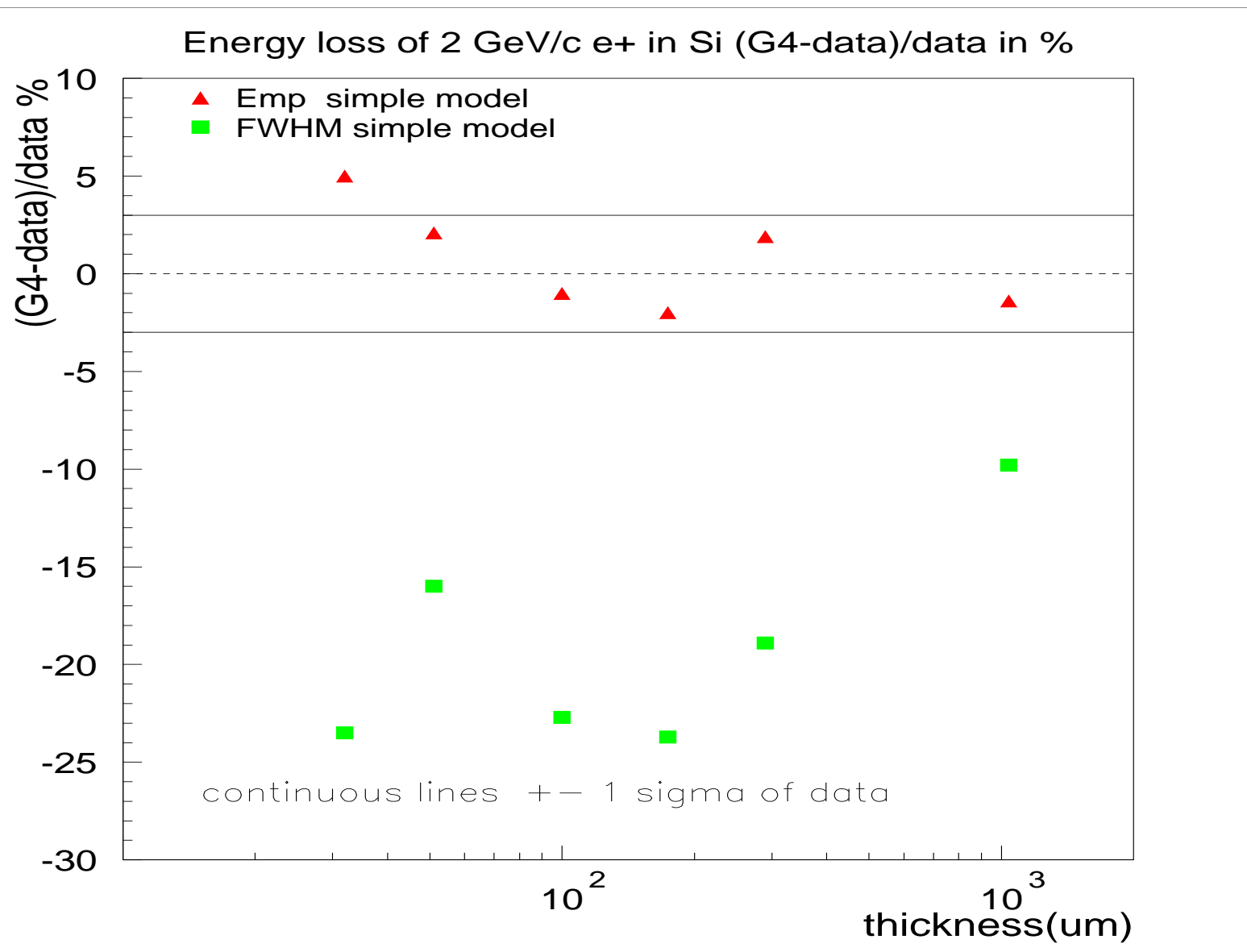
Very simple fluctuation model : 2 energy levels with energy ϵ_1, ϵ_2

energy loss : excitation with energy loss ϵ_1 or ϵ_2

ionization with loss distributed according to a spectrum $1/\epsilon^2$

It gives good peak position, E_{mp} , but the *FWHM* width of the energy loss distribution is too small.

see next slide



some kind of width correction algorithm needed

basic idea: we have to scale somehow the number of excitations and the excitation energies ϵ_1, ϵ_2 in such a way that the mean (discrete) energy loss should be the same as before

—→ the width of the distribution will change

we have to use some data in order to tune the width (high energy e^+/e^- in Si counters).

there are many possibilities for such an algorithm.

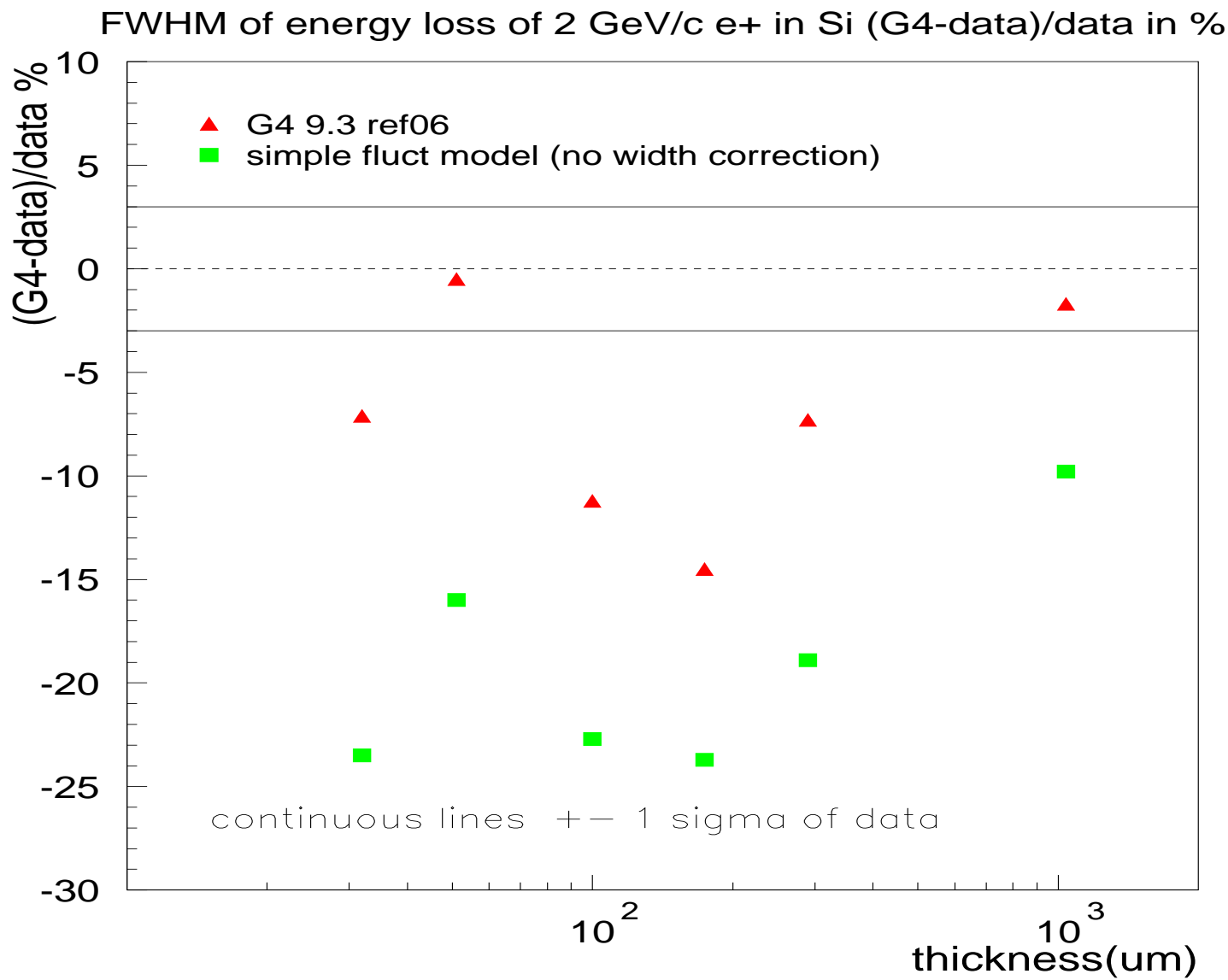
empirical width correction in the model (starting from Geant4 version 9.0)

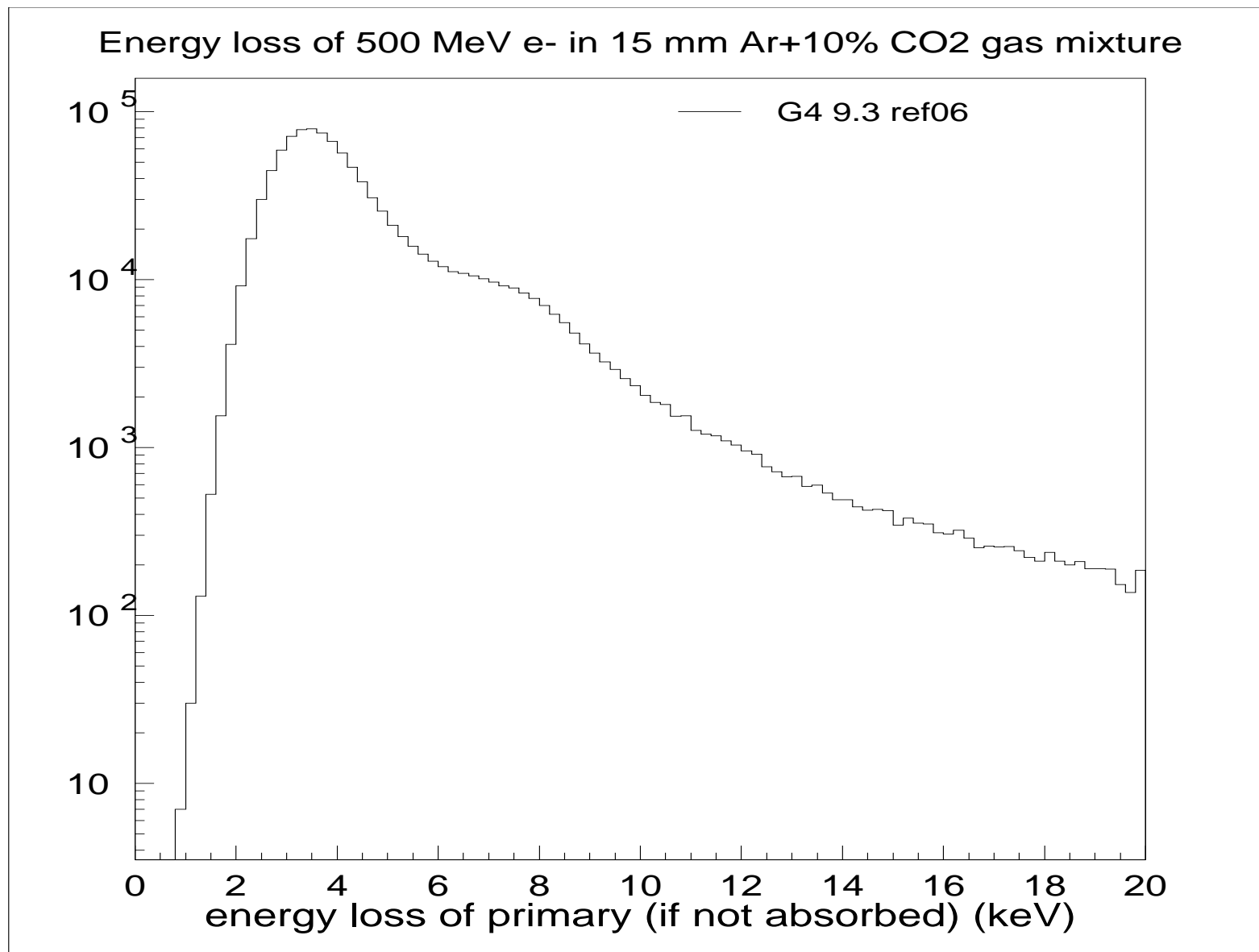
width correction algorithm can depend on the mean loss, the material and the number of excitation with energies ϵ_1, ϵ_2 .

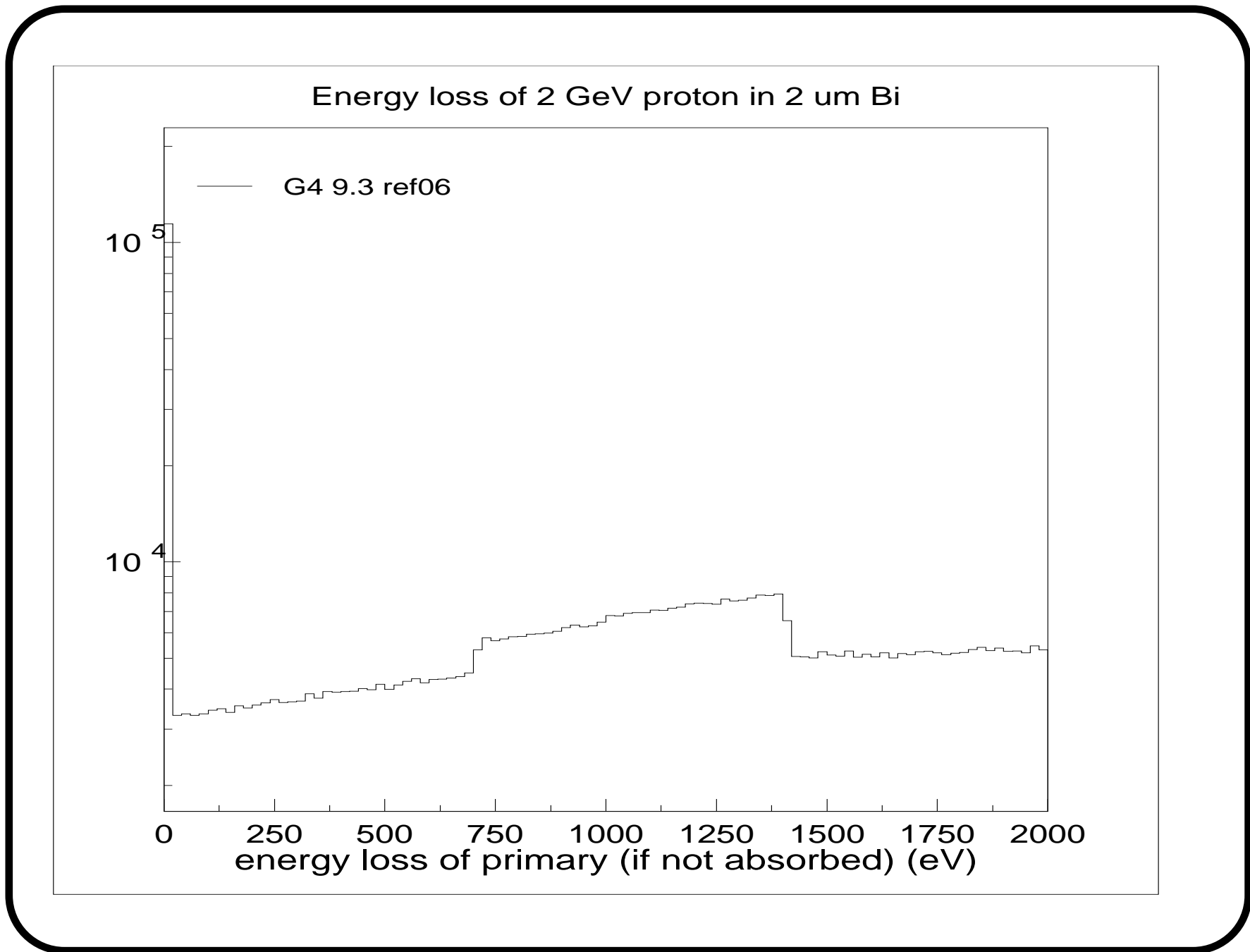
width correction in Geant4 9.3 ref06 gives better FWHM values for high energy particles passing through Si counters than the simple model without width corrections,

but it has several problems

- FWHM values are better than in simple model, but not good
 - shape of the energy loss distribution has an unphysical shoulder for thin target
 - shape of the loss distr. is bad for extreme thin targets
- next slides





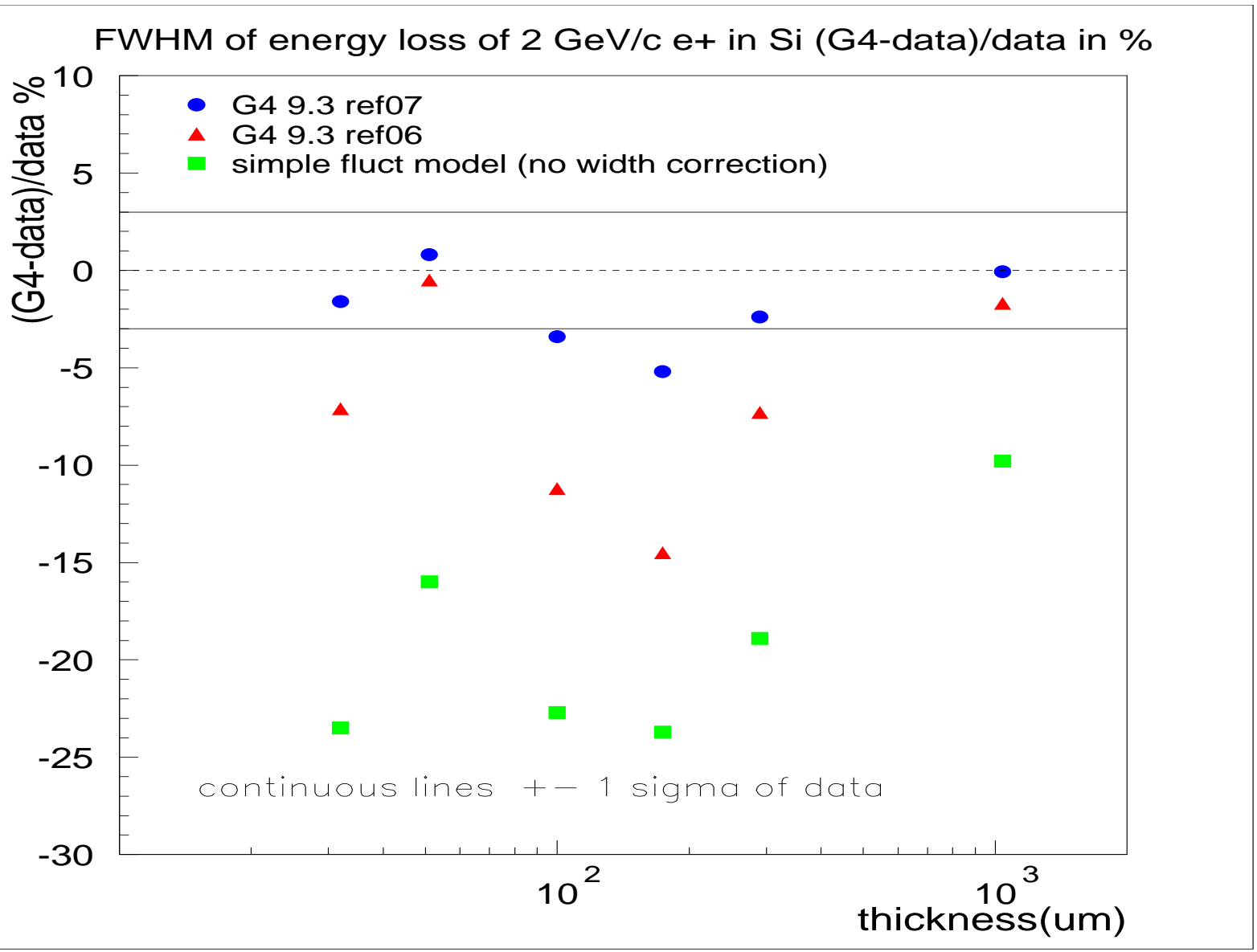


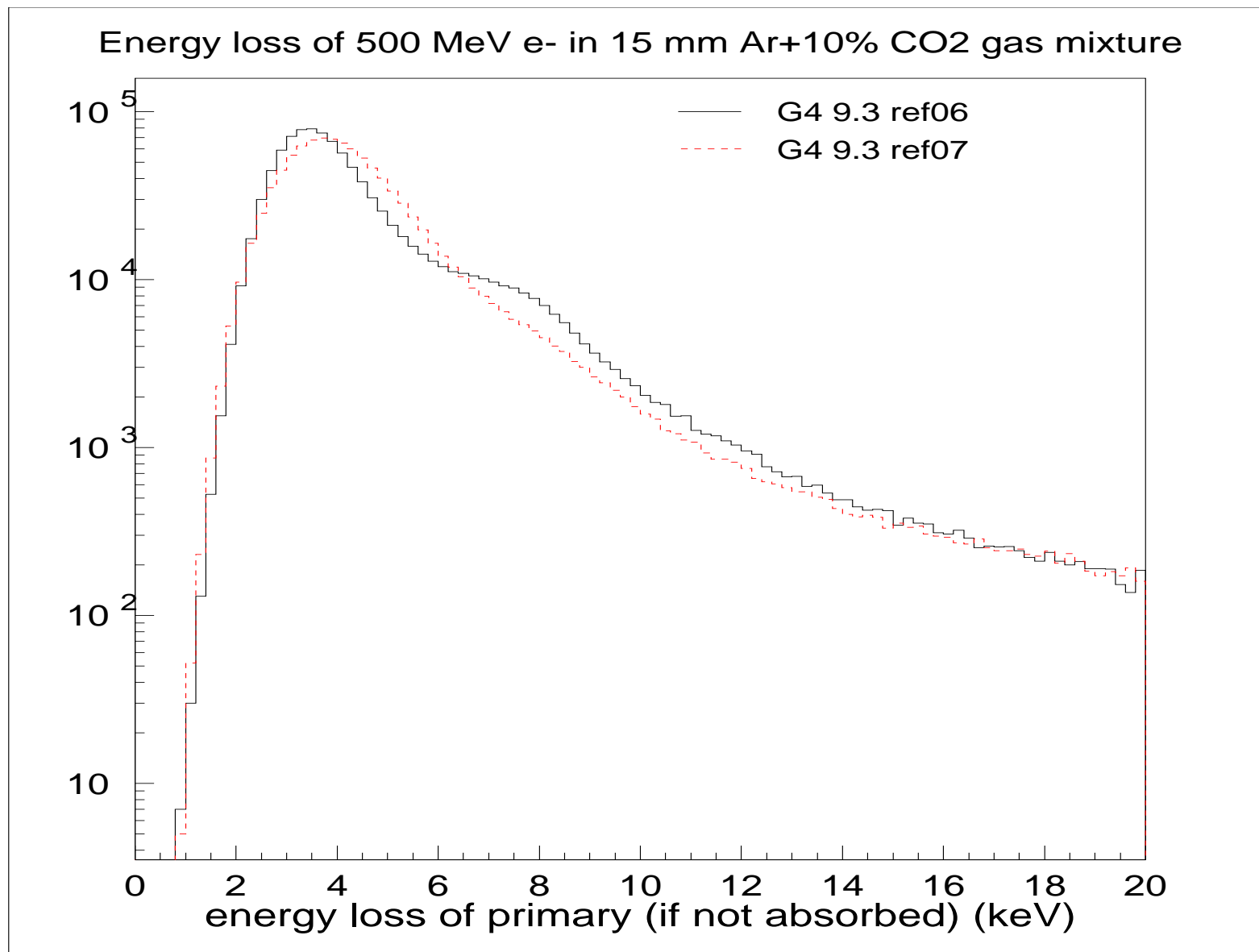
Geant4 9.3 ref07: new width correction algorithm to cure the problems of the fluct. model in ref06

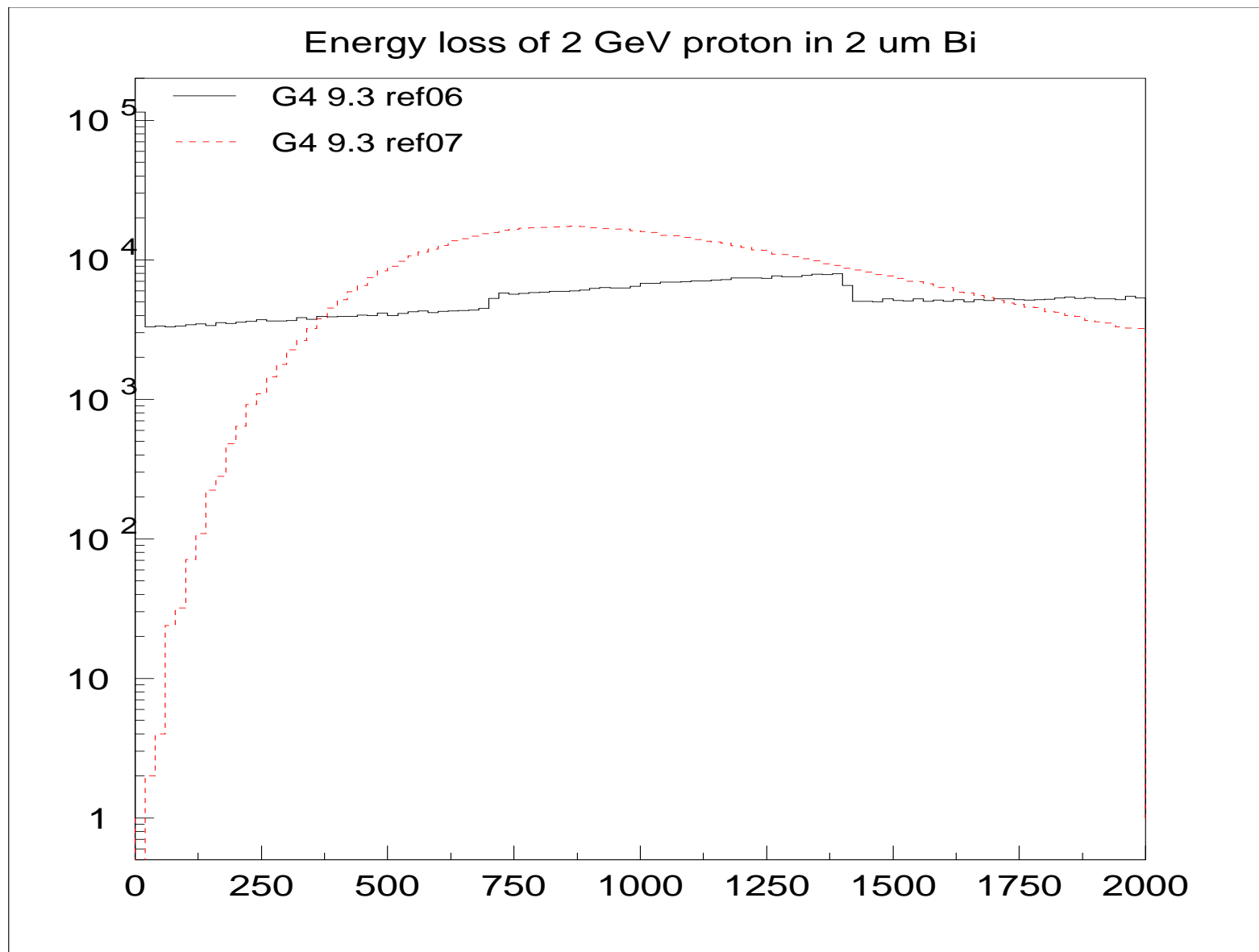
the algorithm does not depend on the mean energy loss in the step, it depends on the material and the number of excitation with energies ϵ_1 , ϵ_2

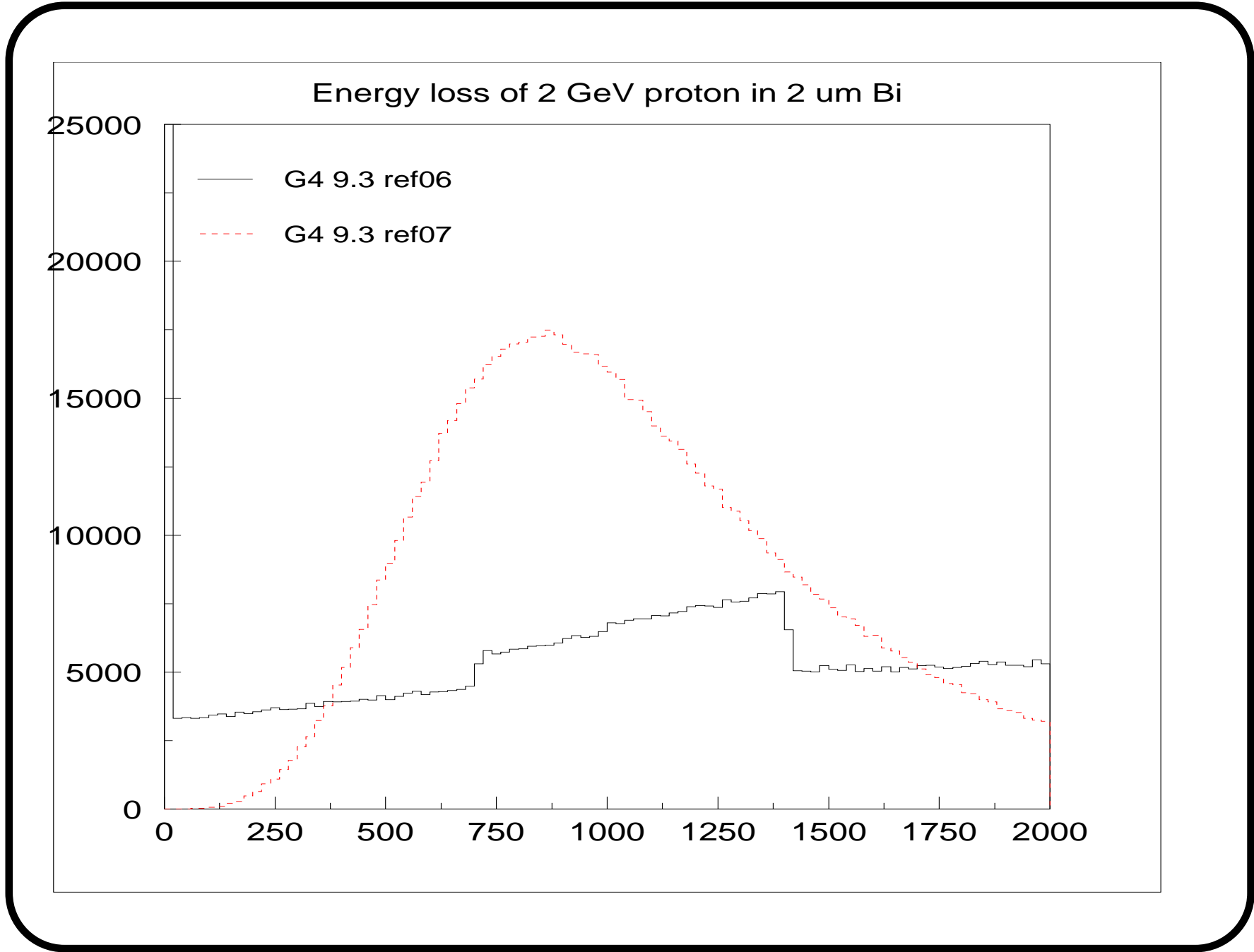
and it is not the same technically than it was in ref 06.

some results are in the following slides..









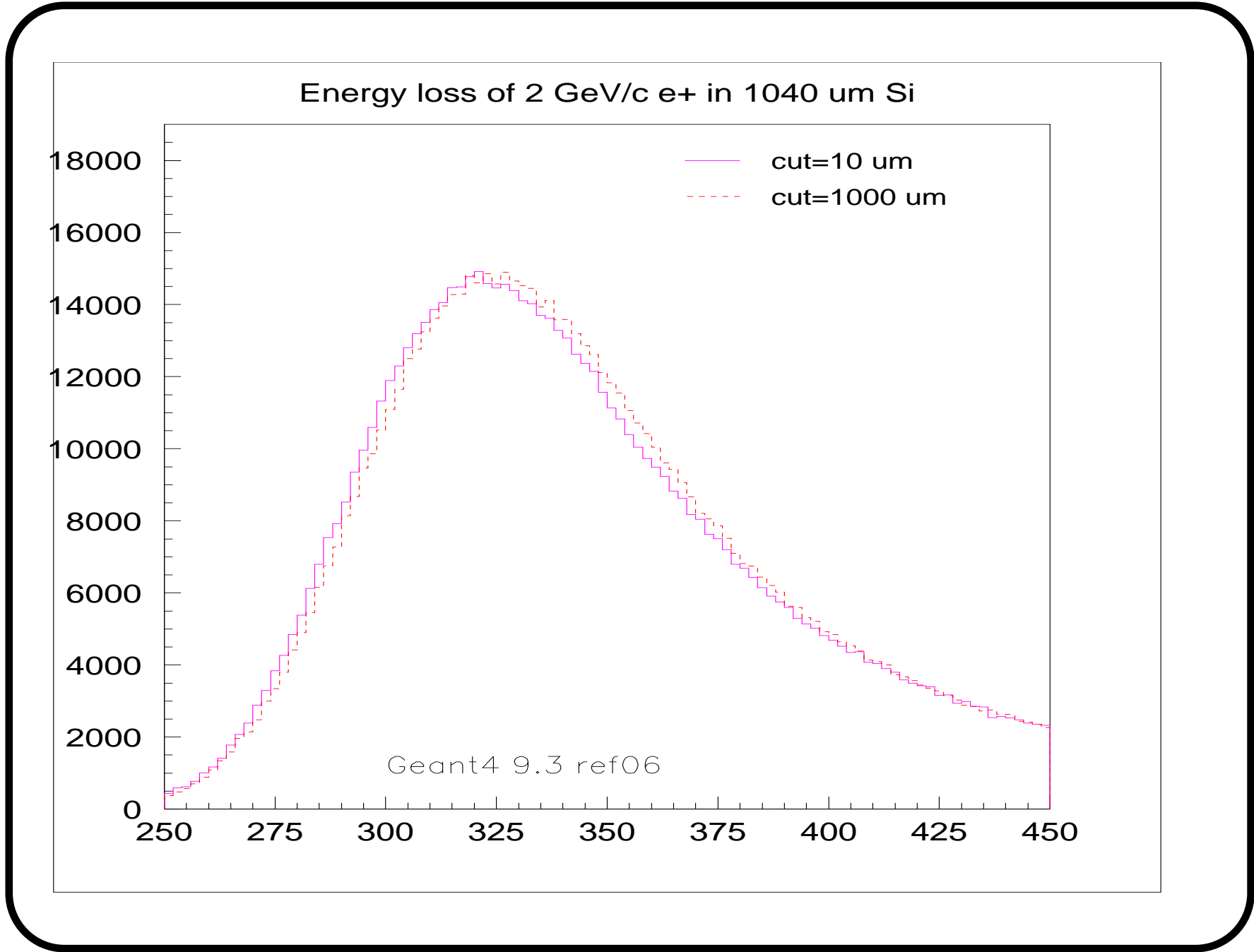
Other results/tests

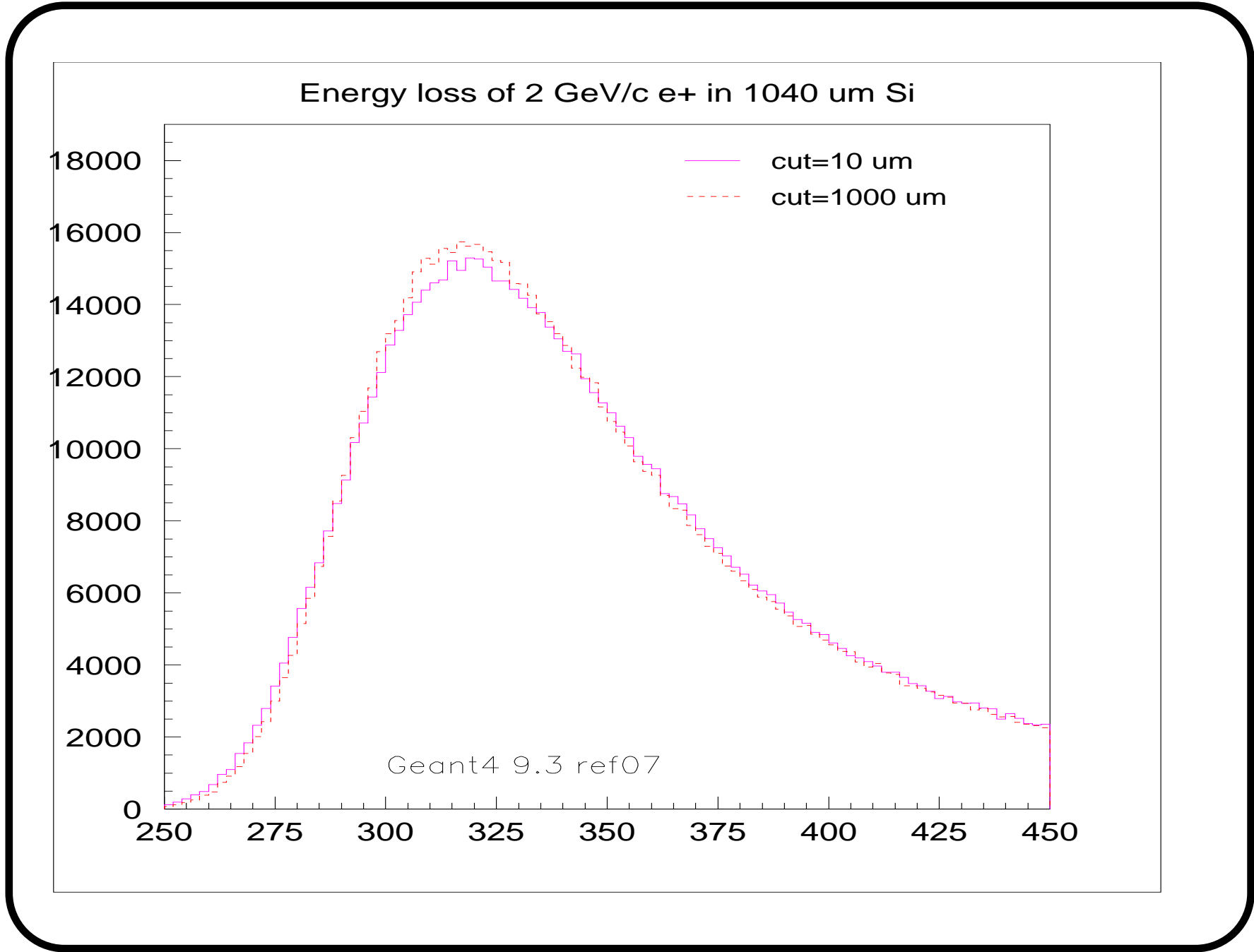
Cut dependence: 2 GeV/c e+ in 1040 um Si, cut=10 um and 1000 um.

weak cut dependence in ref06

the dependence weaker in ref07

see next 2 slides





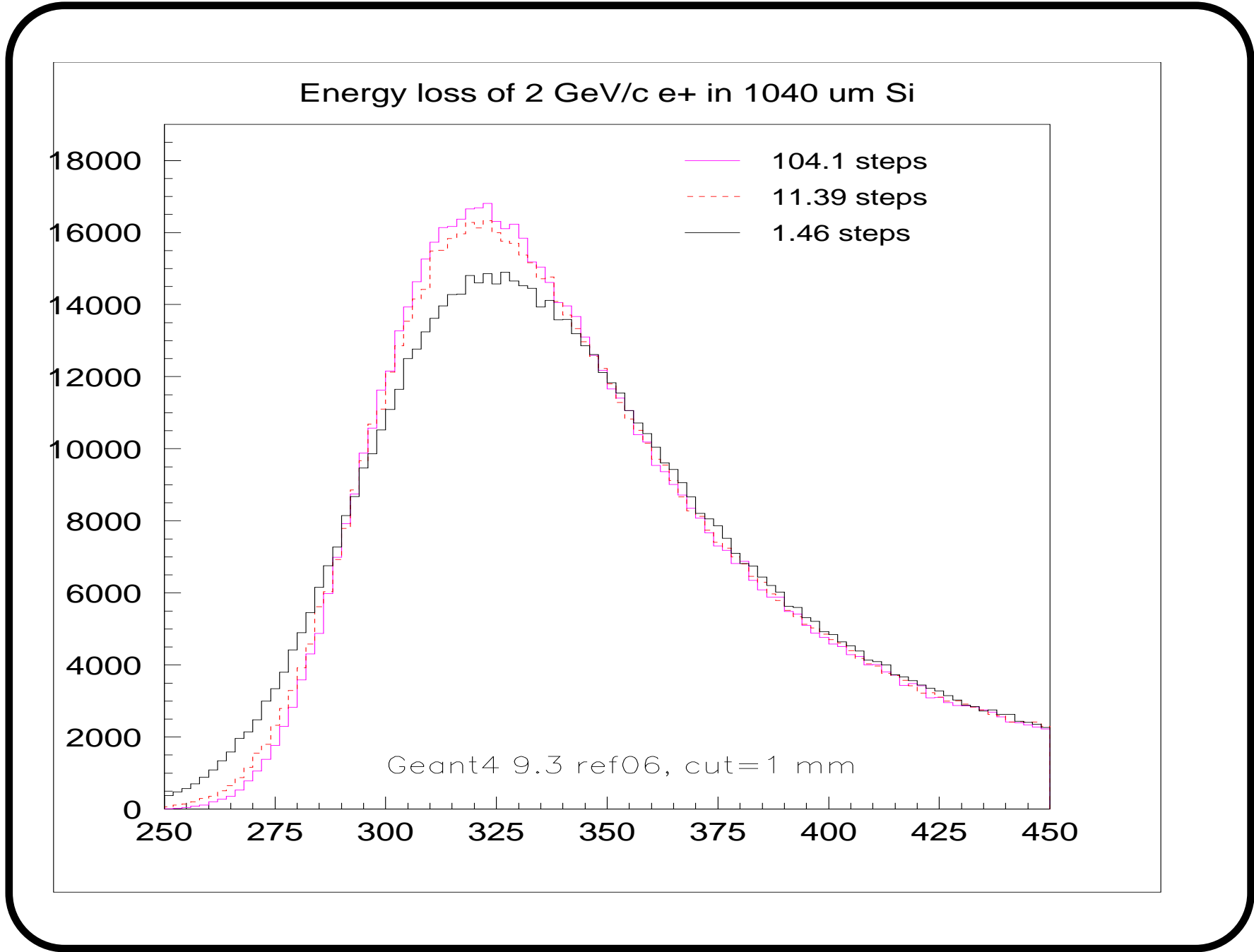
Other results/tests

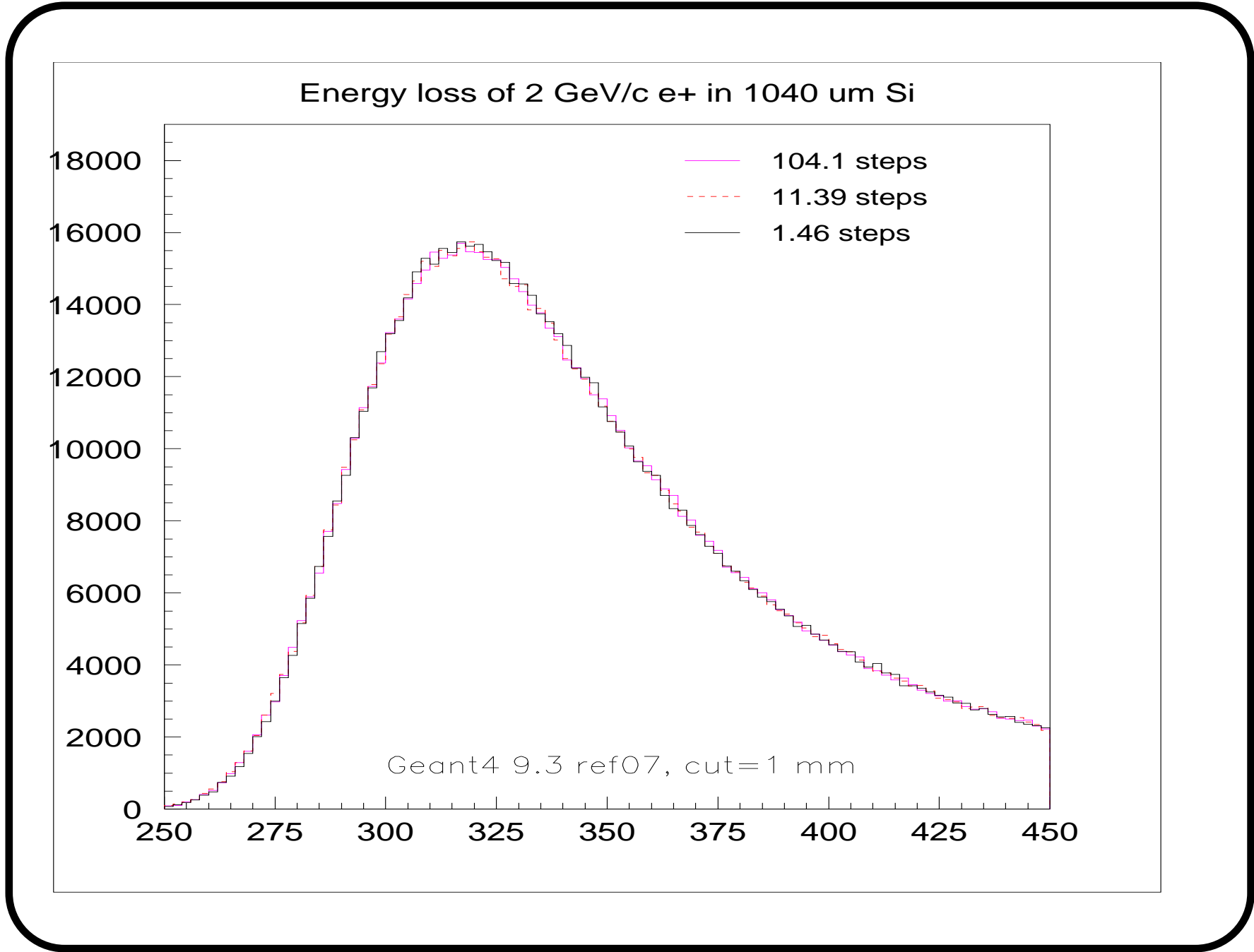
Step dependence: 2 GeV/c e+ in 1040 um Si, no stepmax,
stepmax=104 um, stepmax=10.4 um

step dependence in ref06

practically no step dependence in ref07

see next 2 slides





FWHM has been tuned using e⁺/e⁻ data in silicon.

What about E_{mp} and $FWHM$ in other materials ?

Geant4 9.3 ref07 results only, data - simulation comparisons

Table 1: E_{mp} in MeV for e- energy losses

target	t(g/cm2)	Tkin (MeV)	data	error	theory	Geant4
Li	2.715	150.	3.78	0.12	3.81	3.80
Be	0.748	15.7	0.95	0.02	0.94	0.94
C	1.820	150.	2.78	0.09	2.73	2.70
Al	0.859	15.7	1.11	0.02	1.15	1.15
Cu	0.840	15.7	0.98	0.02	1.00	1.01
Pb	1.135	11.5	1.25	0.10	1.14	1.26

Table 2: *FWHM* MeV for e- energy losses

target	t(g/cm ²)	T _{kin} (MeV)	data	error	theory	Geant4
Li	2.715	150.	0.90	0.01	0.78	0.82
Be	0.748	15.7	0.20	0.02	0.20	0.21
C	1.820	150.	0.81	0.01	0.67	0.66
Al	0.859	15.7	0.27	0.02	0.27	0.29
Cu	0.840	15.7	0.28	0.02	0.27	0.29
Pb	1.135	11.5	—	—	0.63	0.66

The results of the simulation seem to be OK, when the simulation differs from data it agrees with the theory as written down in ref. 2. and 3.

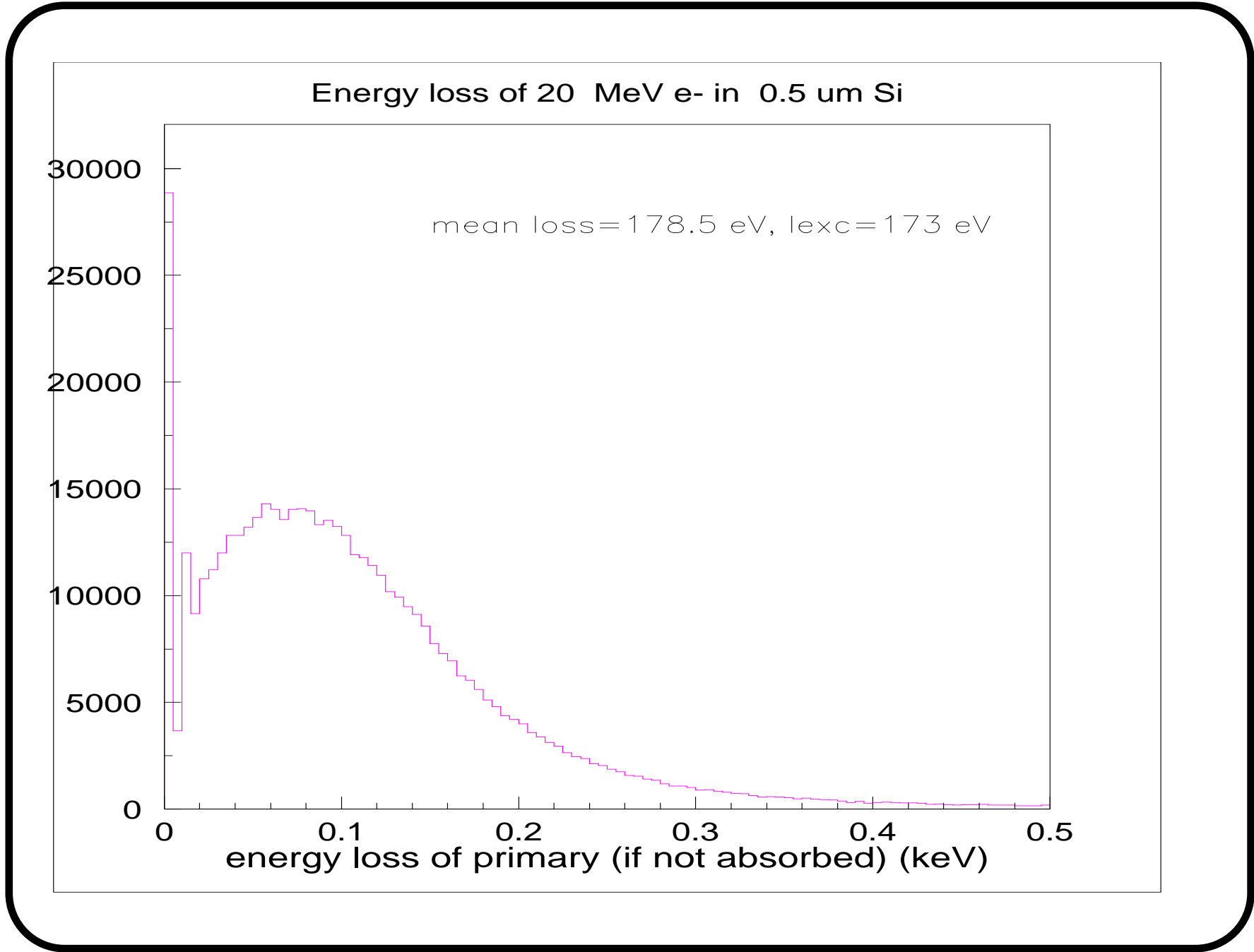
Limits of validity of the model

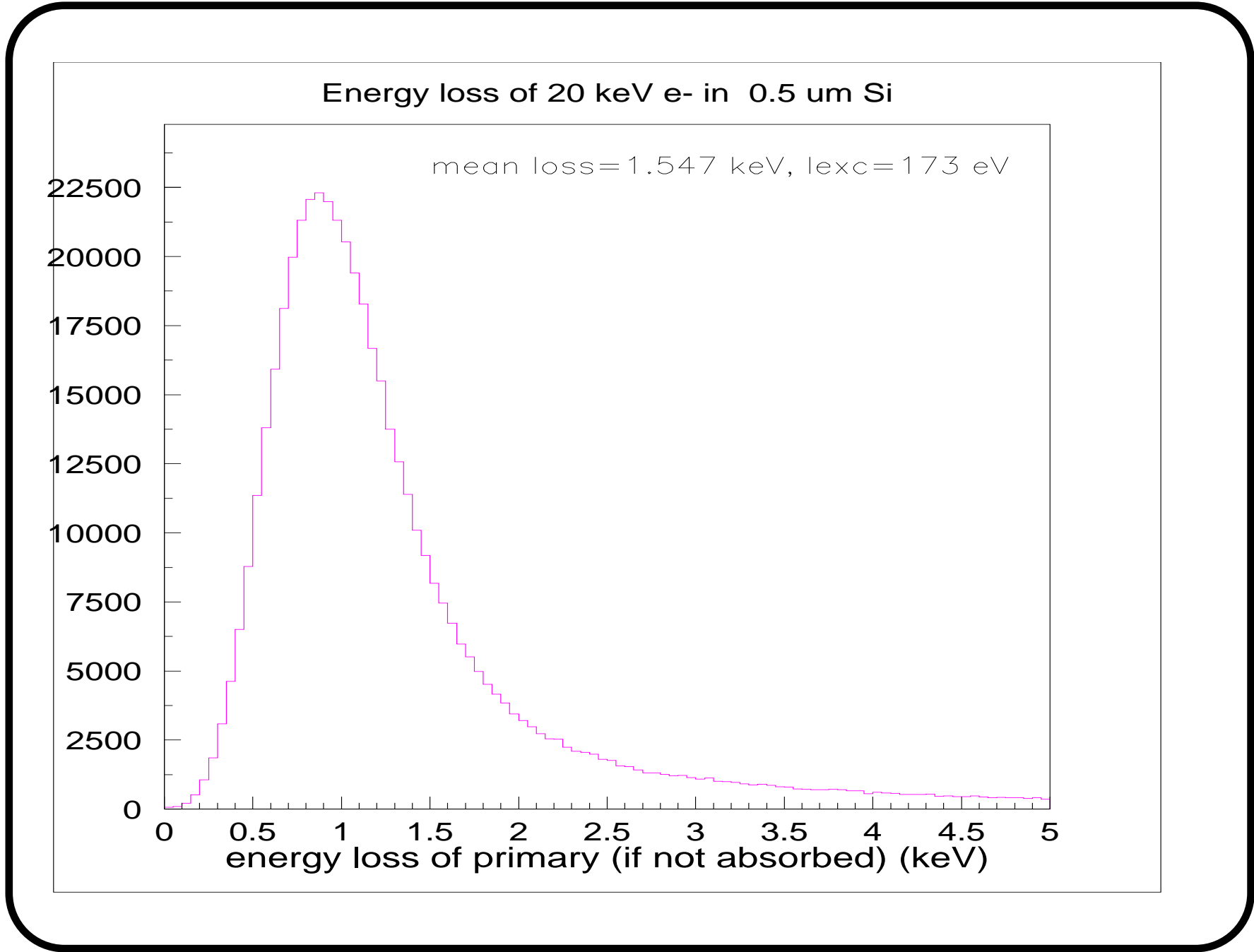
Thick targets : model approaches the Gaussian mode smoothly

Thin targets : the limit is not in thickness of the target

the model gives good (reliable) energy loss distribution if the mean energy loss in the target is \geq (few times)* I_{exc} , where I_{exc} is the mean excitation energy of the target.

examples on next 2 slides





References (energy loss distribution data)

1. H.Bichsel, Rev.Mod.Phys., Vol 60 (1968) p. 663-698. (theory for Si losses+ Si data)
2. J.L. Matthews at al. NIM 180 (1981) p. 573-579. (e- energy loss distributions)
3. Y. Mejaddem at al. NIM B 173 (2001) p. 397-410. (e- energy loss distributions).